**Anodization and characterization of titanium electrodes for electrolytic capacitors**

**Introduction:**  
  
This paper introduces a custom circuitry solution to anodizing and characterizing titanium capacitors.  
  
Electrolytic capacitors are used in a myriad of different applications that we see in our every day lives. They appear in everything from switching power converters to signal filtering. The global aluminum electrolytic capacitor market is projected to grow to $4.2 billion by 2015 (quote: aluminum association). This is a large market for a potential competitor of much higher energy density and a comparable price.

|  |  |  |
| --- | --- | --- |
| Metal | Dielectric Constant | Relative Capacitance uF/cm^2 |
| Ta | 27 | 1 |
| Nb | 48 | 1.3 |
| Al | 10 | .43 |
| Ti | 107 | 1.2 |

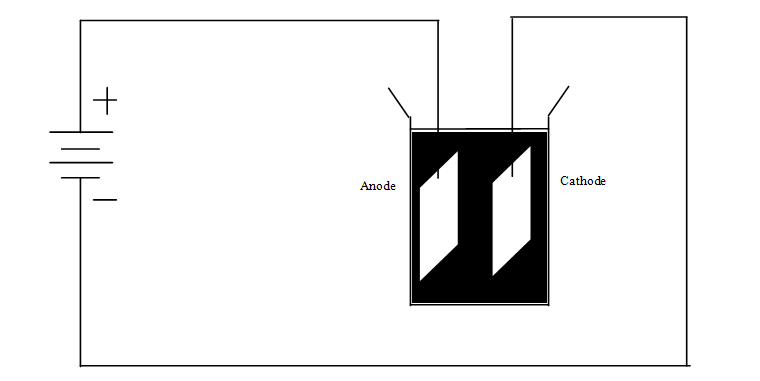
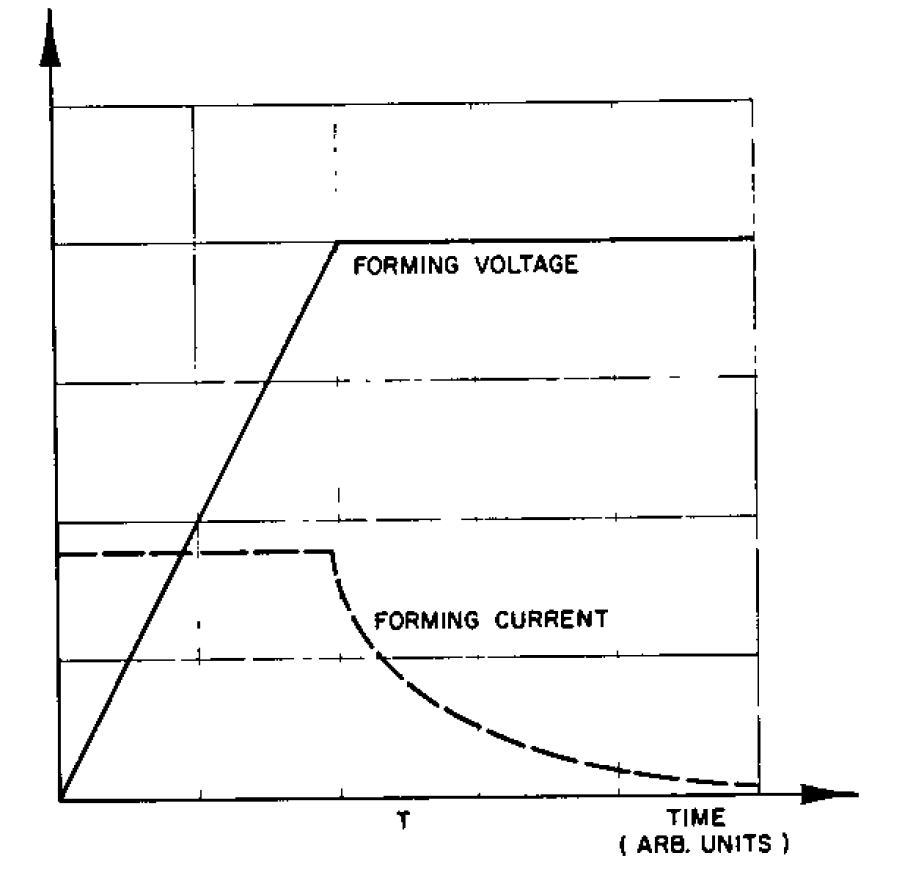
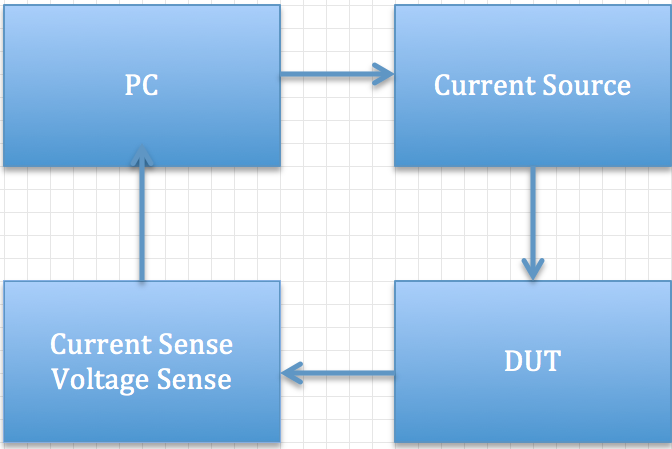
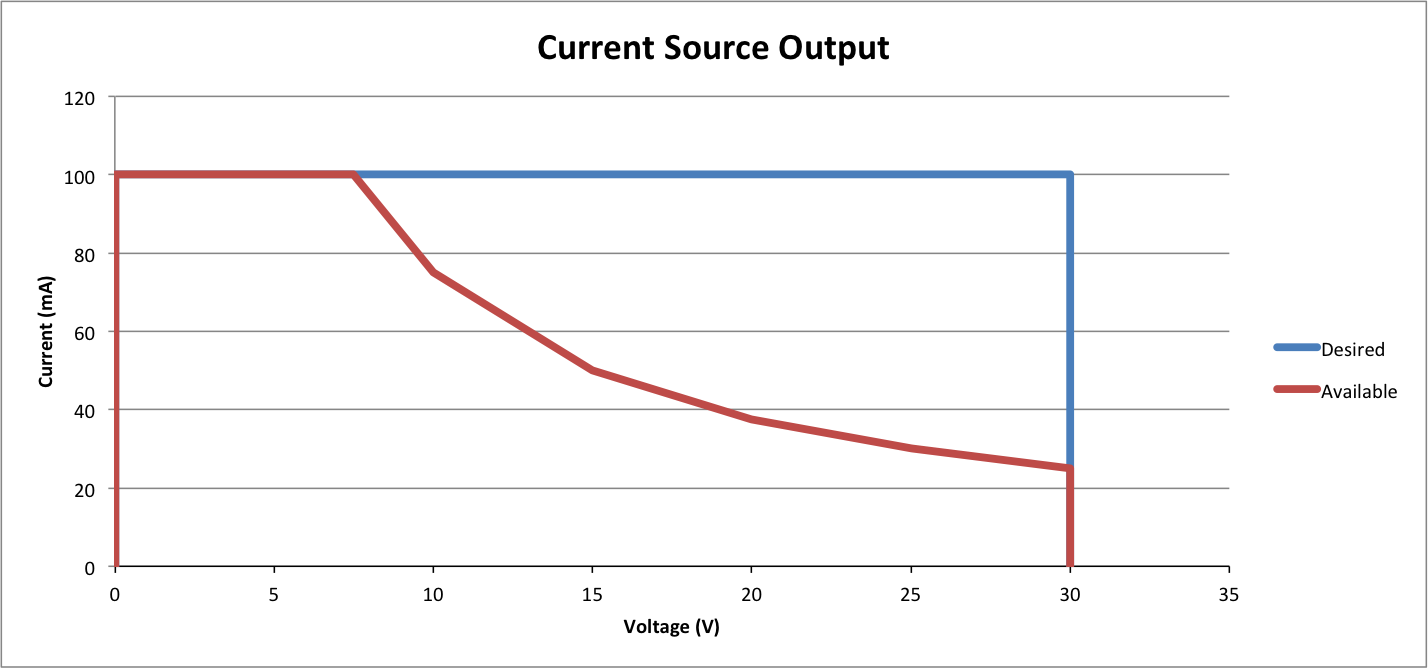
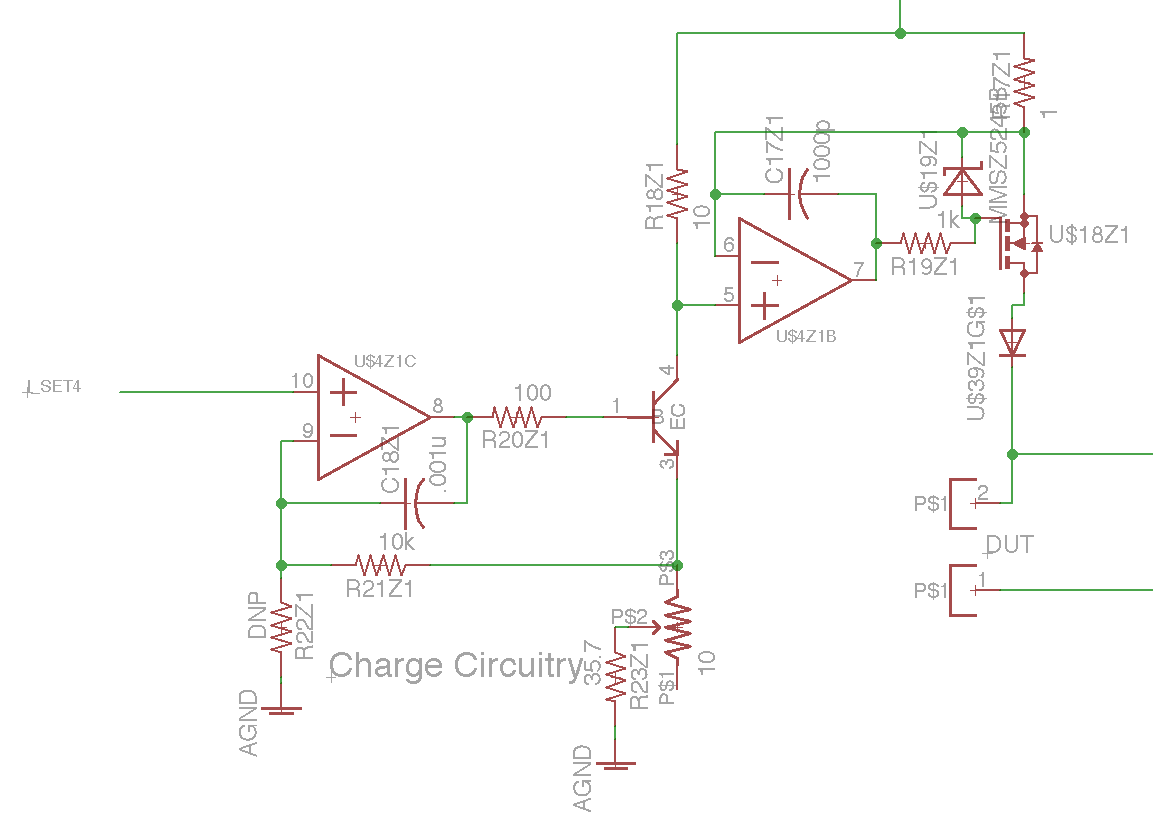
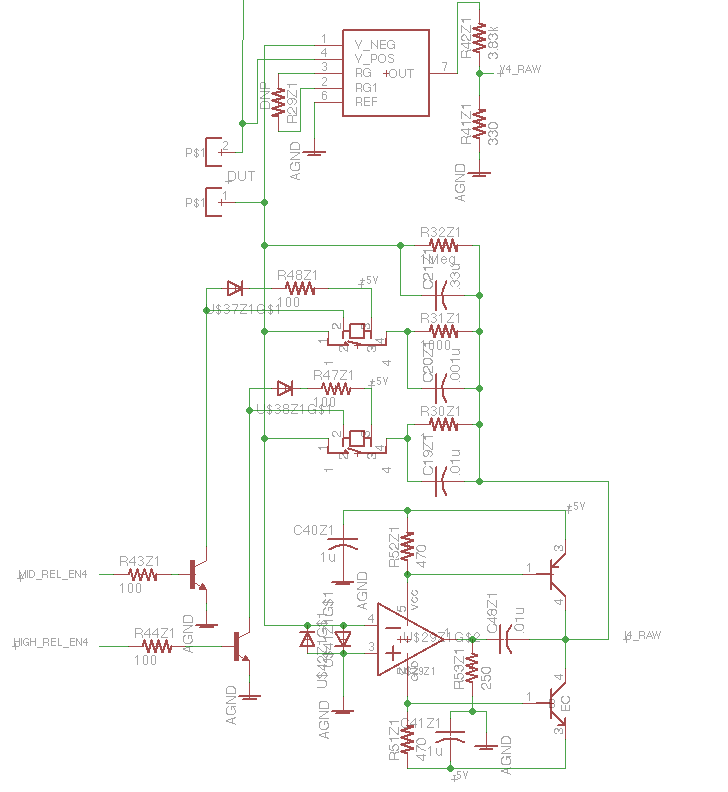
\*Characteristics of titanium electrolytic capacitors  
Fig #1.  
  
Referring to Fig#1, Titanium has the advantages of a dielectric constant over twice as large as its competitors and a relative capacitance 3 times as large as aluminum and comparable to niobium. In the past, titanium capacitors have been plagued by high leakage currents and high ESR. Making them unsuitable for applications in power conversion circuitry. But research by (quote printed caps and welsch’s 1pager) suggests that these obstacles can be overcome by proper cleaning of the titanium anodes and by depositing a sponge like titanium surface onto a substrate to act as an anode. Current research suggests that leakage currents as low as 1uA/cm^2 should be able to be reached by these new methods. (quote microminiturization).  
  
**Anodization Process and Requirements**  
  
Anodization itself is the act of growing an oxide layer on top of a metal anode. This is useful in capacitors because it allows the capacitor to store significantly more energy then it would have otherwise. The anodization process is preformed by immersing an anode and a cathode into an electrolyte solution and then hooking up either a voltage or current source across the sample. This process can be seen in fig#:  
  
 (quote source - Steve’s thesis)  
 Fig #1  
  
Referring to Fig#1, in the simplest case, the current transfer is an ionic transfer where the Ti anode reacts with O2 to create a TiO2 oxide layer. The reaction at the metal-oxide surface can be written as:  
  
Ti + 02 => TiO2 + 4e (equ. 1)  
  
The titanium also reacts with the electrolyte solution to give off hydrogen:  
  
Ti + 2H20 => Ti02 + 4H+ (equ 2)  
  
This hydrogen reacts with the electrons at the cathode to create hydrogen gas and complete the ionic circuit.  
  
4H + 4e => 2H2 (equ 3)  
  
  
This process is very similar to anodizing aluminum. For an explanation of that process visit (---quote Case encyclopedia).   
  
  
**Considerations and Requirements for Titanium Anodization**  
  
While anodizing titanium for purposes of making capacitors, there are a number of requirement that need to be followed. Since the rate of oxide formation is dependent on the charge transport into the anode during anodization, a current source was selected. A typical anodization process with a current source will see the current and voltage progress as in Fig#2  


Fig #2

(quote microminiturization)

If a constant current is introduced, the voltage will (ideally) rise linearly with time. This will happen until the DUT reaches the compliance voltage, at which point the current through the DUT will begin to drop off until it reaches the leakage current of the unpackaged capacitor.   
  
  
**Design and Implementation of Custom System Used for Anodization**  
  
  
The overall system flow can be see in fig #. A computer is used to configure a current source that supplies a stable current to a DUT (Device Under Test) up to a specified voltage compliance. The current through and voltage across the DUT is measured and logged to the computer for post processing.

**Computer**

The computer scripts were written in Python and are in charge of configuring the hardware for each test and logging data being sent from the board.  
  
 **Current Source**  
  
The range of values of interest in this application are 1-30V and 1-100mA.   
  
The basic circuitry has two main parts, sourcing and measurement. The current source has the ability to supply 1-100mA of current at a voltage of 1-30V. The actual safe operating region is depicted in the following graph.  
  
  
Portions of the desired operating area are curtailed in order to stay within the safe power limits of the pass transistors. Further development is planned to increase the operating range, by actively calculating the power dissipation in the pass transistors. The current calculations are done based upon worse case, open loop, scenarios.  
  
The current source is made up if an op-amp controlled current mirror.  
  
  
  
The left leg of the mirror is controlled by a DAC set by a microcontroller. It is mirrored at a x10 rate on the right side. The current source can provide current up until the voltage of the DUT reaches the compliance voltage, which is defined as the voltage at the top of the current mirror minus several small voltage drops.  
  
 **DUT**  
  
The device under test was typically meant to be a titanium anode to be anodized or a titanium capacitor. The device is able to operate with resistive loads and any capacitive loads (with capacitance large enough for the system to be able to respond.  
  
 **Current and Voltage Measurements**  
  
The second part of the circuitry is measurement side. The voltage is measured by a differential amplifier chip across the DUT, while the current is measured by a transimpedance amplifier.  
  
  
Since it is desirable the measure both the anodization current and the leakage current afterwards, a basic transimpedance amplifier design was modified to include 3 switched feedback paths. This allows the current measurement to measure currents over 8 orders of magnitude. The circuitry can handle currents from 10nA to 100mA.  
  
In this way, the circuitry can measure both the current and voltage of the DUT in real time. Both the voltage and current are filtered by Butterworth filters in the Sallen-Key topology. After filtering, the signals are fed into ADCs on the microcontroller and digitized. The microcontroller is an Atmel ATxMega64a3, with 12 bit ADCs, giving a resolution of:

|  |  |  |
| --- | --- | --- |
| **Resolution** | **Full scale measurement** | **Comment** |
| **7.32mA** | **30V** |  |
| **.098mA** | **100mA** | **Hi current measurement** |
| **.98uA** | **1ma** | **Med current measurement** |
| **.98nA** | **1uA** | **Lo current measurement.\*** |

\*This measurement is before calculations of external noise and temperature variations.  
  
Once the data is collected onto the microcontroller, it is sent to a PC via USB for further analysis. The data is sampled by the ADCs at a rate of #baud and transferred to the PC at a rate of 2Mbaud. This allows for maximum flexibility on the PC side, where any data coming in at a rate greater than what is desired can simply be discarded.  
  
**III. Experimental procedures.  Describe the open beaker anodization.**  
  
The experimental setup to anodize the anode of a titanium capacitor with the aforementioned circuitry is as follows. The anode sample is prepared by cleaning the surface oxide off with a chemical bath. It is then transported into a beaker of anodizing solution. The current source is connected to the DUT and acts as both a current source and data logger until the test is over.ent through the DUT has dropped to the leakage current  
  
  
**IV. Experimental results.  This can be a selection of the materials Don and Laurie have anodized.  To date I am not sure if we really have any from Don.**  
  
To date this method has anodized a number of different materials, including the following list:

|  |  |  |  |  |  |  |  |  |
| --- | --- | --- | --- | --- | --- | --- | --- | --- |
| **Test ID** | **Anode Material** | **Cathode Material** | **Electrolyte** | **Anodizing Current** | **Anodizing Compliance Voltage** | **Leakage Current (uA - 1kHz)** | **Series Resistance (ohms - 1kHz)** | **Capacitance (uF - 1kHz)** |
|  | **Ti2** | **Ti** | **1% H3PO4** |  |  |  |  |  |
| **06202011A** | **ZrIt 20/80** | **Ti** | **1%H3PO4** |  |  |  |  |  |
| **07052011E** | **ZrTi 20/80** |  | **1%H3PO4** |  |  |  |  |  |
| **07012011A** | **ZrTi 80/20** |  |  |  |  |  |  |  |
| **07012011B** | **ZrTi 50/50** |  |  |  |  |  |  |  |
| **06202011A** | **ZrTi 50/50** |  |  |  |  |  |  |  |
| **06202011B** | **ZrTi 50/50** |  |  |  |  |  |  |  |
| **06082001#3** | **Ti** |  | **5%H3PO4** | **20mA** | **30V** |  |  |  |